



DMN5L06VK/VAK

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

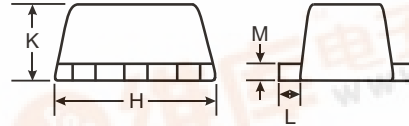
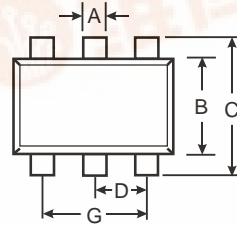
NEW PRODUCT

Features

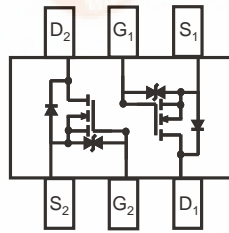
- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **ESD Protected Up To 2kV**

Mechanical Data

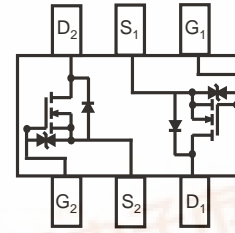
- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking: Date Code and Type Code, See Page 2
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	
All Dimensions in mm			



DMN5L06VK
(KAB Type Code)



DMN5L06VAK
(KAE Type Code)



ESD protected up to 2kV

Maximum Ratings @ T_A = 25°C unless otherwise specified

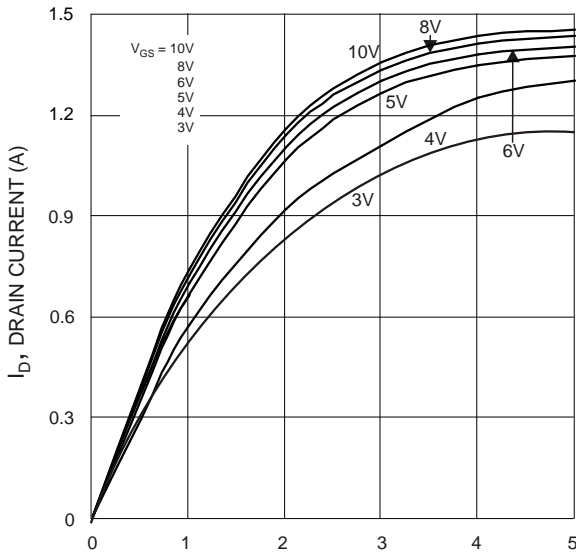
Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{bss}	50	V
Drain-Gate Voltage R _{GS} 1.0M	V _{DGR}	50	V
Gate-Source Voltage	V _{GSS}	±20 ±40	V
Drain Current (Note 1)	I _D	280	mA
Drain Current (Note 1)	I _{DM}	1.5	A
Total Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{JA}	833	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

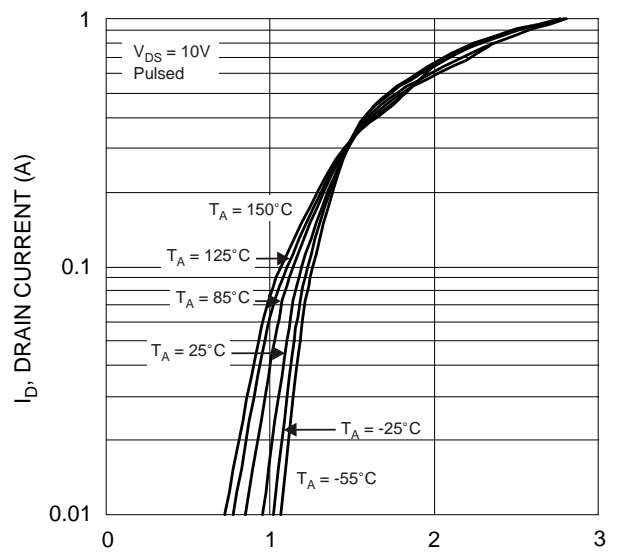


Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	50			V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = 25^\circ\text{C}$	I_{DSS}			60	nA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}			1 500 50	μA nA nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	0.49		1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$			3.0 2.5 2.0		$V_{GS} = 1.8V, I_D = 50mA$ $V_{GS} = 2.5V, I_D = 50mA$ $V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current	$I_{D(ON)}$	0.5	1.4		A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200			mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	V_{SD}	0.5		1.4	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}			50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}			25	pF	
Reverse Transfer Capacitance	C_{rss}			5.0	pF	



V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Fig. 1 Typical Output Characteristics



V_{GS} , GATE-SOURCE VOLTAGE (V)
Fig. 2 Typical Transfer Characteristics

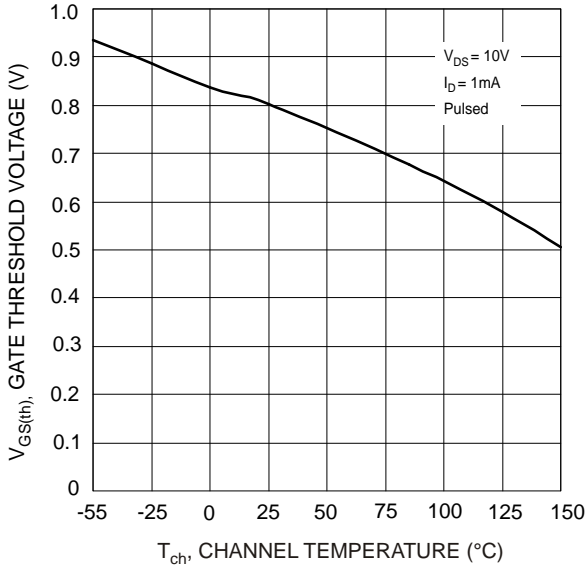


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

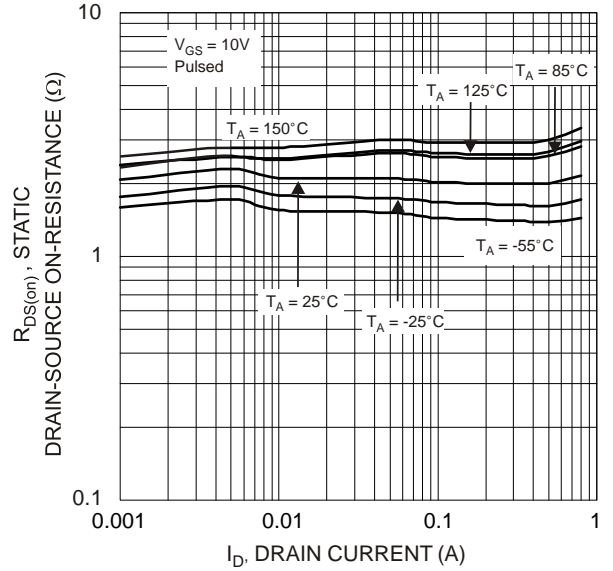


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

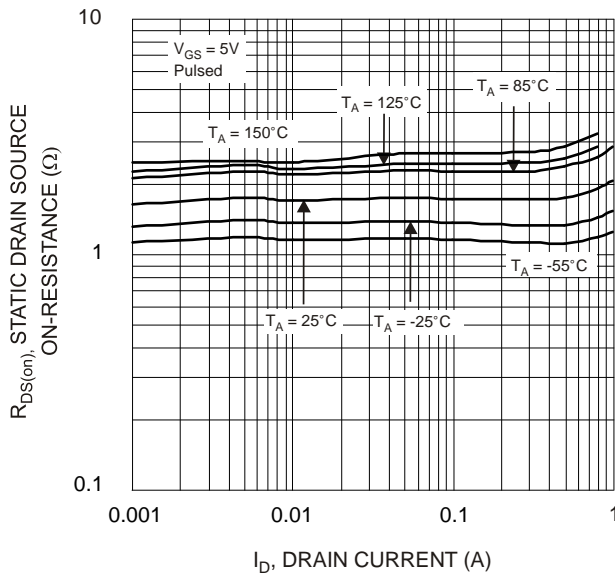


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

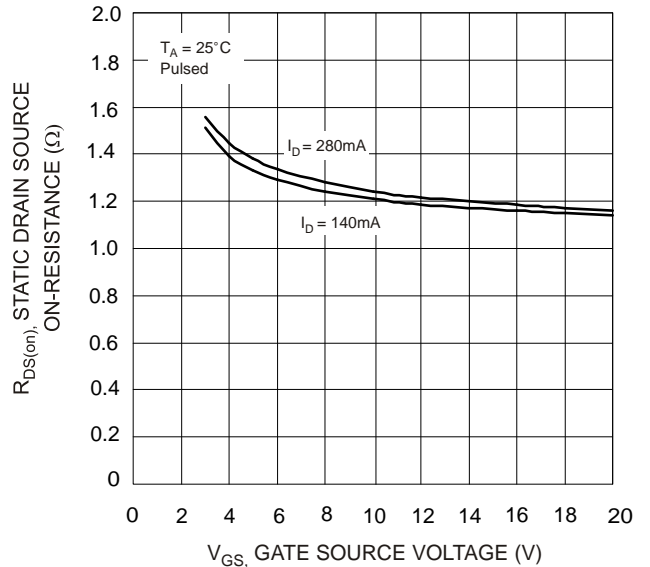


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

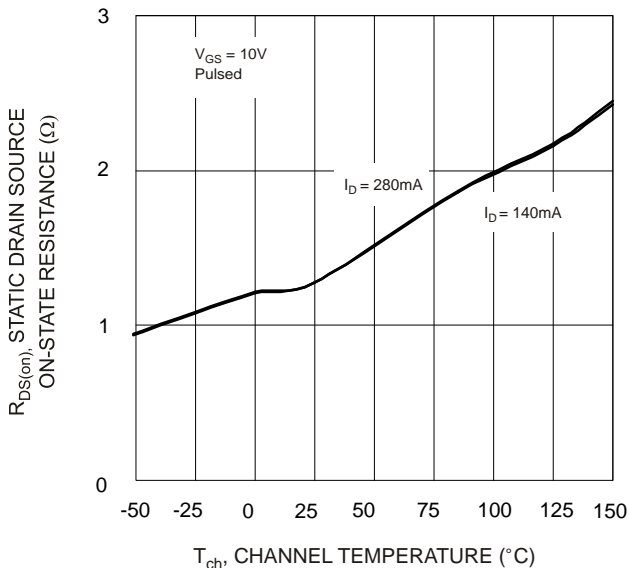


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

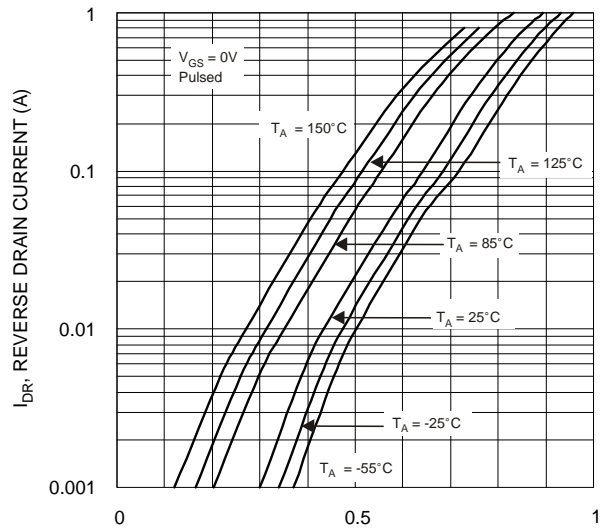


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

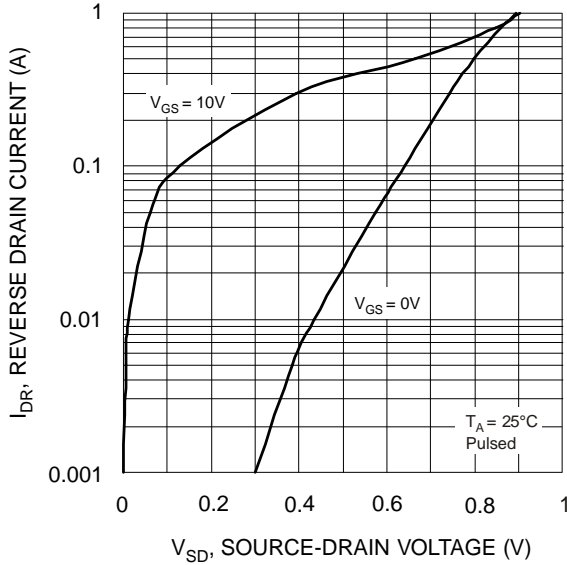


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

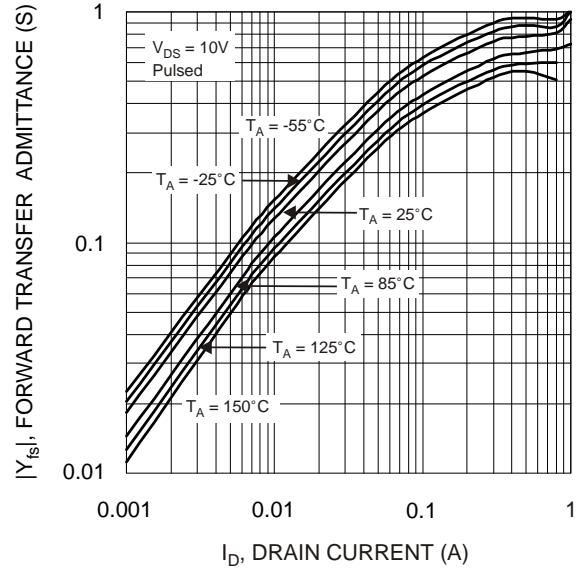


Fig. 10 Forward Transfer Admittance vs. Drain Current

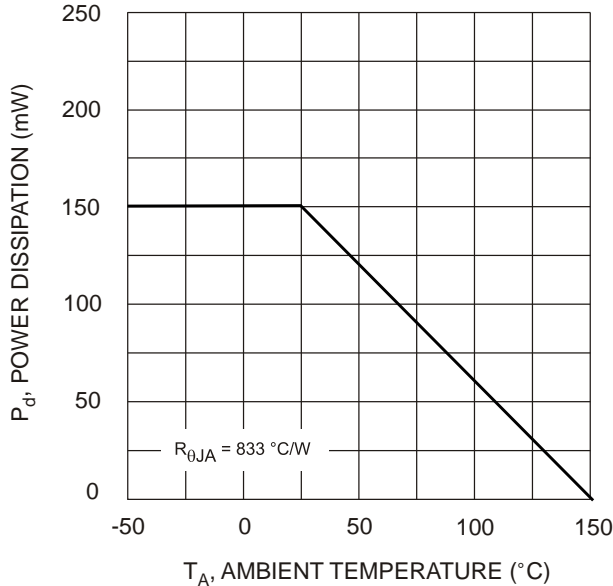


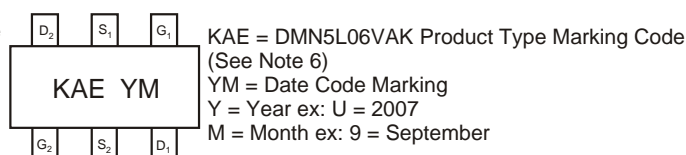
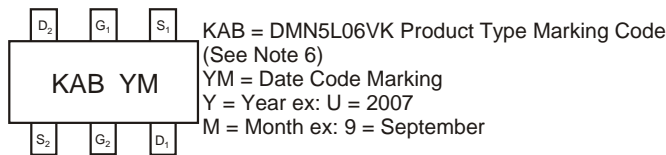
Fig. 11 Derating Curve - Total

Ordering Information (Note 5)

Device	Packaging	Shipping
DMN5L06VK-7	SOT-563	3000/Tape & Reel
DMN5L06VAK-7	SOT-563	3000/Tape & Reel

- Notes: 4. Short duration test pulse used to minimize self-heating effect.
5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information (Note 6)



- Notes: 6. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Date Code Key

Year	2006			2007			2008			2009		
Code	T			U			V			W		
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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